

L Number	Hits	Search Text	DB	Time stamp
13	5041	((438/149) or (438/311) or (438/459) or (438/584) or (438/706) or (438/758) or (438/795) or (438/909) or (438/935)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/18 20:21
14	37845	(hold or holding) near portion	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/18 20:22
15	20782	SOI or (silicon adj on adj insulator)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/18 20:23
16	23846	reducing near atmosphere	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/18 20:23
17	805976	hydrogen	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/18 20:23
18	2	((hold or holding) near portion) same (SOI or (silicon adj on adj insulator))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/18 20:24
19	96	((hold or holding) near portion) and (SOI or (silicon adj on adj insulator))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/18 20:24
20	1	((((hold or holding) near portion) and (SOI or (silicon adj on adj insulator))) and (reducing near atmosphere))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/18 20:24
21	1	(((((hold or holding) near portion) and (SOI or (silicon adj on adj insulator))) and (reducing near atmosphere)) and hydrogen	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/18 20:24
-	34	silicon adj boat	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 18:41
-	34	silicon adj boat	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 11:08
-	60174	silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 18:18
-	92082	cvd	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 18:18
-	2120	(silicon adj carbide) same cvd	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 18:18

-	66246	boat	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 18:18
-	41	((silicon adj carbide) same cvd) same boat	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 18:18
-	34	silicon adj boat	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/21 19:44
-	1	((((silicon adj carbide) same cvd) same boat) and (silicon adj boat)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 18:43
-	74	((((silicon adj carbide) same cvd) same boat) or (silicon adj boat)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 18:43
-	14400	soi	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/21 19:43
-	34	silicon adj boat	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/21 19:44
-	1	soi same (silicon adj boat)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/21 19:46
-	1146922	semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/21 19:50
-	5	(silicon adj boat) same semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/21 19:46
-	12	semiconductor adj on adj insulat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 18:28
-	14562	soi	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/02 11:04
-	508529	transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/02 11:04
-	3801	soi same transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/02 11:04

-	60532	silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/02 11:04
-	10	(soi same transistor) same (silicon adj carbide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 18:28
-	15468	soi or (silicon near2 insulator)	USPAT; US-PGPUB	2003/05/18 20:25
-	265	silicon near2 boat	USPAT; US-PGPUB	2003/05/18 20:25
-	14	((soi or (silicon near2 insulator)) and (silicon near2 boat))	USPAT; US-PGPUB	2003/05/18 20:26
-	13	((soi or (silicon near2 insulator)) and (silicon near2 boat)) and @ad<20020307	USPAT; US-PGPUB	2003/05/18 20:27
-	1	("6468884").PN.	USPAT; US-PGPUB	2003/10/29 10:53
-	4619	((438/149) or (438/311) or (438/459) or (438/584) or (438/706) or (438/758) or (438/795) or (438/909) or (438/935)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/18 20:21
-	405	(silicon or ((single near2 crystal) adj silicon) or (poly near2 silicon) or (silicon near2 carbide)) near2 boat	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 14:33
-	20	((((438/149) or (438/311) or (438/459) or (438/584) or (438/706) or (438/758) or (438/795) or (438/909) or (438/935)).CCLS.) and ((silicon or ((single near2 crystal) adj silicon) or (poly near2 silicon) or (silicon near2 carbide)) near2 boat))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 14:26
-	100	(silicon near2 carbide) near2 boat	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 18:29
-	8	((((438/149) or (438/311) or (438/459) or (438/584) or (438/706) or (438/758) or (438/795) or (438/909) or (438/935)).CCLS.) and ((silicon near2 carbide) near2 boat))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 14:33
-	0	6296709.URPN.	USPAT	2003/11/07 14:37
-	5	("4640223" "4964378" "5001327" "5029554" "6139642").PN.	USPAT	2003/11/07 14:37
-	7513	(soi or (semiconductor adj on adj insulat\$3)) near2 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 18:29
-	100	(silicon near2 carbide) near2 boat	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 18:30
-	2	((soi or (semiconductor adj on adj insulat\$3)) near2 substrate) same ((silicon near2 carbide) near2 boat)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/07 18:30